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June 2015

FL663 Primary-Side-Regulation PWM Controller for LED Illumination

Features

- Low Standby Power: < 30 mW
- High-Voltage Startup
- Few External Component Counts
- Constant-Voltage (CV) and Constant-Current (CC)
 Control without Secondary-Feedback Circuitry
- Green-Mode: Linearly-Decreasing PWM Frequency with Cycle skipping.
- Fixed PWM Frequency at 50 kHz and 33 kHz with Proprietary Frequency Hopping to Solve EMI Problems
- Peak-Current-Mode Control in CV Mode
- Cycle-by-Cycle Current Limiting
- V_{DD} Over-Voltage Protection (OVP)
- V_{DD} Under-Voltage Lockout (UVLO)
- Adjustable Brownout Detector
- Gate Output Maximum Voltage Clamped at 15 V
- Thermal Shutdown (TSD) Protection
- Available in the 8-Lead SOIC Package

Applications

- LED Illumination
- Battery chargers for cellular phones, cordless phones, PDA, digital cameras, power tools

Description

This third-generation Primary-Side-Regulation (PSR) and highly integrated PWM controller provides features to enhance the performance of LED illumination.

The proprietary topology, TRUECURRENT®, enables precise CC regulation and simplified circuit for LED illumination applications. The result is lower-cost and smaller LED lighting compared to a conventional design or a linear transformer.

To minimize standby power consumption, the proprietary green-mode function provides off-time modulation to linearly decrease PWM frequency with cycle skipping under light-load conditions. Green mode assists the power supply in meeting the power conservation requirements.

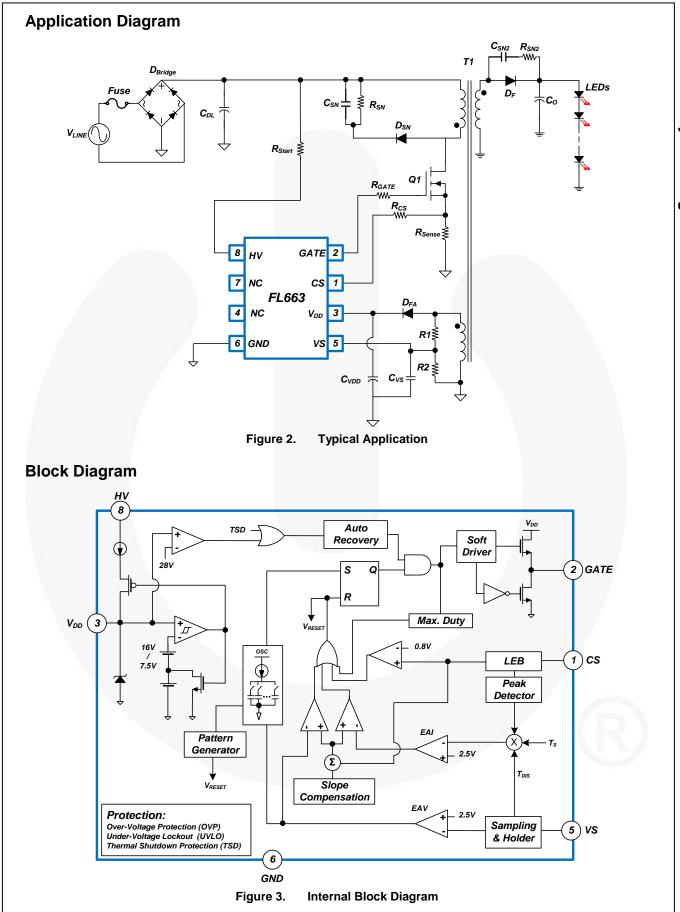
By using the FL663, LED illumination can be implemented with few external components and minimized cost.



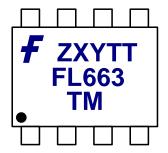
Figure 1. 8-Lead SOIC

Ordering Information

Part Number	Operating Temperature Range		Package	Packing Method
FL663MX	-40°C to +125°C	FL663	8-Lead, Small-Outline Package (SOIC-8)	Tape & Reel



Marking Information



F: Fairchild Logo

Z: Plant Code

X: 1-Digit Year Code

Y: 1-Digit Week Code

TT: 2-Digit Die Run Code

T: Package Type (M=SOP)
M: Manufacture Flow Code

Figure 4. Top Mark

Pin Configuration

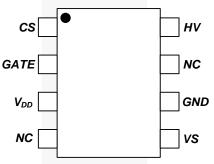


Figure 5. Pin Configuration

Pin Definitions

Pin#	Name	Description			
1	CS	Current Sense . This pin connects a current-sense resistor to detect the MOSFET current for peak-current-mode control in CV Mode and provides the output-current regulation in CC Mode.			
2	GATE	PWM Signal Output . This pin uses the internal totem-pole output driver to drive the power MOSFET. It is internally clamped below 15 V.			
3	V _{DD}	Power Supply . IC operating current and MOSFET driving current are supplied using this pin. This pin is connected to an external V_{DD} capacitor of typically 10 μ F. The threshold voltages for startup and turn-off are 16 V and 7.5 V, respectively. The operating current is lower than 5 mA.			
4	NC	No Connect . This pin is connected to GND or no connection. Does not connect any voltage source.			
5	VS	Voltage Sense . This pin detects the output voltage information and discharge time based on voltage of auxiliary winding.			
6	GND	Ground			
7	NC	No Connect			
8	HV	High Voltage . This pin connects to DC link capacitor for high-voltage startup. This pin is connected to an external startup resistor of typically 100 k Ω .			

Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol	Parameter			Max.	Unit
V _{HV}	HV Pin Input Voltage			500	V
V_{VDD}	DC Supply Voltage ⁽¹⁾			30	V
V _{VS}	VS Pin Input Voltage	-0.3	6.0	V	
Vcs	CS Pin Input Voltage	-0.3	6.0	V	
P _D	Power Dissipation (T _A <50°C)		660	mW	
θ_{JA}	Thermal Resistance, (Junction-to-A		+150	°C/W	
θЈС	Thermal Resistance, (Junction-to-Case)			39	°C/W
TJ	Junction Temperature		-40	+150	°C
T _{STG}	Storage Temperature Range		-55	+150	°C
TL	Lead Temperature (Wave Soldering or IR, 10 Seconds)			+260	°C
ESD ⁽²⁾	51 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	Human Body Model (Except HV Pin), JEDEC-JESD22_A114		5.0	1.37
	Electrostatic Discharge Capability	Charged Device Model (Except HV Pin), JEDEC-ESD22_C101	\\	2.0	kV

Notes:

- 1. All voltage values, except differential voltages, are given with respect to GND pin.
- 2. All Pins: HBM=1 kV, CDM=1.25 kV

Recommended Operating Conditions

The Recommended Operating Conditions table defines the conditions for actual device operation. Recommended operating conditions are specified to ensure optimal performance to the datasheet specifications. Fairchild does not recommend exceeding them or designing to Absolute Maximum Ratings.

Symbol	Parameter	Min.	Тур.	Max.	Unit
V_{DD}	Continuous Operating Voltage			25	V
T _A	Operation Ambient Temperature	-40		+125	°C

Electrical Characteristics

 V_{DD} =15 V and T_A =-40°C~125°C unless otherwise noted.

Symbol	Parameter		Conditions	Min.	Тур.	Max.	Unit
V _{DD} Section	•			JI.	JI.	ı	
$V_{DD\text{-}ON}$	Turn-On Thr	eshold Voltage		15	16	17	V
V _{DD-OFF}	Turn-Off Thr	eshold Voltage		7.0	7.5	8.0	V
I _{DD-OP}	Operating C	urrent			3.2	5.0	mA
I _{DD-GREEN}	Green Mode	Operating Supply Current			0.95	1.20	mA
$V_{DD\text{-}OVP}$	V _{DD} Over-Vo	Itage Protection Level		27	28	29	V
t _{D-VDDOVP}	V _{DD} OVP De	bounce Time		90	200	350	μs
High Voltage	(HV) Section	1					
V _{HV-MIN}	Minimum Sta	artup Voltage on HV Pin ⁽³⁾				50	V
I _{HV}	Supply Curre	ent Drawn from Pin HV	V _{DL} =100 V	1.0	2.0	5.0	mA
I _{HV-LC}	Leakage Cu	rrent after Startup	HV=500 V, V _{DD} =V _{DD-OFF} +1 V		0.5	3.0	μΑ
Oscillator Se	ction	y/-		\			
	Normal	Center Frequency	> V _O * 0.5, T _A =25°C	47	50	53	kHz
	Frequency	Frequency Hopping Range		±1.5	±2.0	±2.5	
fosc	Protection Frequency ⁽⁴⁾	Center Frequency	< V _O * 0.5, T _A =25°C		33		
		Frequency Hopping Range			±1.3		
V _{F-JUM-53}	Frequency Jumping Point		50 kHz → 33 kHz, VS ⁽³⁾	1.05	1.25	1.55	V
$V_{\text{F-JUM-35}}$			33 kHz → 50 kHz, VS	1.28	1.50	1.75	V
f _{OSC-N-MIN}	Minimum Frequency at No-Load			260	385	500	Hz
f _{OSC-CM-MIN}	Minimum Frequency at CCM			7	12	17	kHz
V _{S-F-SKIPH}	COMV Level Period Chan	l for High Cycle Skipping ge ⁽³⁾	<i></i>		1.14		V
V _{S-F-SKIPL}	COMV level for Low Cycle Skipping period Change ⁽³⁾				0.80		٧
$\triangle COMV_{SKIP}$	Cycle Skippi Voltage	ng Period COMV Hysteresis			0.34		V
_	Cycle Skipping Period ⁽³⁾		V _{S-F- SKIPH} < COMV < V _N		240		
T _{SKIP-CV}			V _{S-F-SKIPL} >COMV		160		ms
f_{DV}	Frequency Variation vs. V _{DD} Deviation ⁽³⁾		V _{DD} =10~25 V		1	2	%
f _{DT}	Frequency Variation vs. Temperature Deviation					15	%
Voltage Sens	se (V _S) Sectio	n	•			1	
V _R	Reference Voltage for Error AMPs		T _A =25°C	2.475	2.500	2.525	V
V _N	Green-Mode Starting Voltage on EAV		f _{OSC} =2 kHz		2.5	1/1	V
V _G	Green-Mode Ending Voltage on EAV		f _{OSC} =1 kHz		0.5		V
V _{BIAS-COMV}	Adaptive Bia	s Voltage Dominated by	R _{VS} =20 kΩ		1.4		V

Continued on the following page...

Electrical Characteristics

 V_{DD} =15 V and T_A =-40°C~125°C unless otherwise noted.

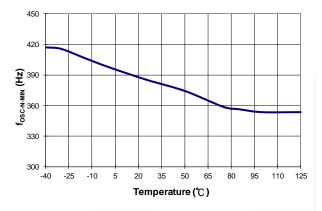
Symbol	Par	ameter	Conditions	Min.	Тур.	Max.	Unit
I _{tc}	IC Bias Current			7.3	10.0	12.7	μA
I _{VS-BO}	Brownout Detection	n Current ⁽⁴⁾			175		μΑ
I _{VS-MIN}	Minimum VS Curre	ent ⁽⁴⁾	90 V _{AC} , Heavy Load		227		μA
I _{VS-MAX}	Maximum VS Current ⁽⁴⁾		264 V _{AC} , No Load		721		μΑ
	Minimum	Normal Operation ⁽⁴⁾	f _{OSC} =50 kHz		0.65		μs
t _{DIS_MIN}	Discharging Time	Protection Area	fosc=33 kHz	2.0	2.6	4.0	
Current Sen	se (CS) Section						
t _{PD}	Propagation Delay	to GATE Output			90	200	ns
t _{MIN-N}	Minimum On Time	at No-Load	V _{COMR} =1 V	800	975	1150	ns
V _{TH}	Threshold Voltage	for Current Limit		0.75	0.80	0.85	V
V_{TL}	Threshold Voltage than 0.5 V	on V _S Pin Smaller		V	0.25		V
GATE Section	on				•		•
DCY _{MAX}	Maximum Duty Cy	cle		60	75	85	%
V _{OL}	Output Voltage Low		V _{DD} =20 V, Gate Sinks 10 mA			1.5	V
V _{OH}	Output Voltage High		V _{DD} =8 V, Gate Sources 1 mA	5			V
t _r	Rising Time		C _L =1 nF		200	250	ns
t _f	Falling Time		C _L =1 nF		60	100	ns
V_{CLAMP}	Output Clamp Volt	age	V _{DD} =25 V		15	18	V
Thermal Shu	utdown (TSD) Section	on		•			
TSD	Thermal Shutdown	n Temperature ⁽⁴⁾		+140			°C
TSD _{HYS}	Thermal Shutdown Hysteresis ⁽⁴⁾				+15		°C

Notes:

- 3. Guaranteed by design.
- 4. These parameters, although guaranteed, are not 100% tested in production.

Typical Performance Characteristics 9.5 17.5 17 8.5 16.5 V_{DD-OFF} (V) 16 7.5 15.5 6.5 15 14.5 5.5 Temperature (°C) Temperature (°C) Figure 6. V_{DD-ON} vs. Temperature Figure 7. V_{DD-OFF} vs. Temperature 58 55 f_{osc} (KHz) I_{DD-OP} (mA) 52 49 46 43 -25 -10 35 50 65 95 110 -25 -10 35 50 110 Temperature (°C) Temperature (°C) Figure 8. I_{DD-OP} vs. Temperature Figure 9. fosc vs. Temperature 1.2 1.12 1.04 (mA) 2.45 -40 50 -25 -10 35 80 110 125 Temperature (°C) Temperature (°C) Figure 11. I_{DD-GREEN} vs. Temperature Figure 10. V_R vs. Temperature

Typical Performance Characteristics (Continued)



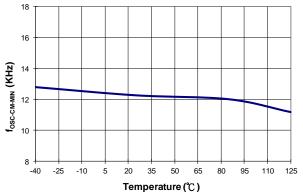
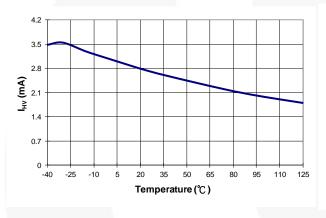


Figure 12. f_{OSC-N-MIN} vs. Temperature





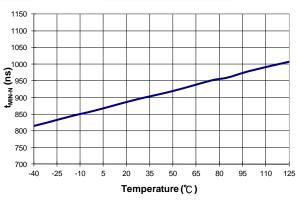
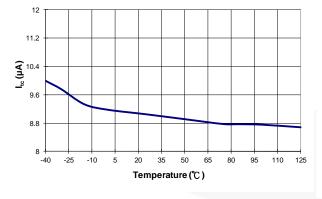


Figure 14. I_{HV} vs. Temperature

Figure 15. t_{MIN-N} vs. Temperature



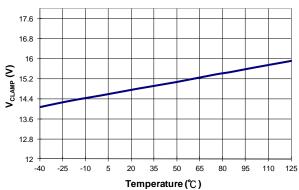


Figure 16. Itc vs. Temperature

Figure 17. V_{CLAMP} vs. Temperature

Typical Performance Characteristics (Continued)

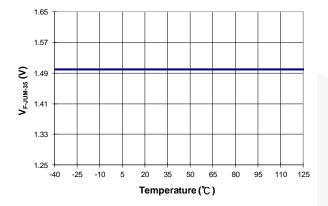


Figure 18. V_{F-JUM-35} vs. Temperature

Functional Description

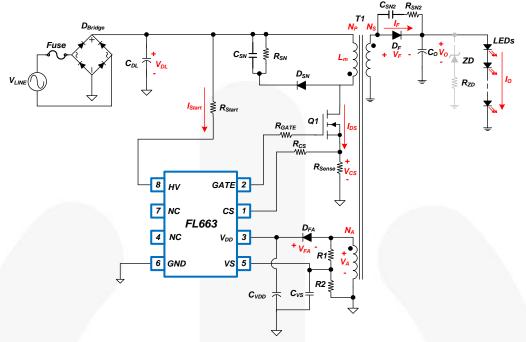


Figure 19. Basic Circuit of a PSR Flyback Converter for LED Illumination

Figure 19 shows the basic circuit diagram of a primary-side regulated flyback converter with typical waveforms shown in Figure 20. Generally, Discontinuous Conduction Mode (DCM) operation is preferred for primary-side regulation since it allows better output regulation.

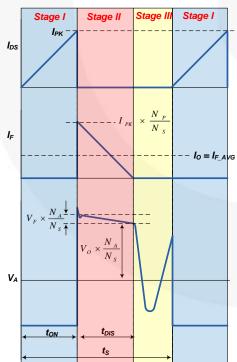


Figure 20. Waveforms of DCM Flyback Converter

The operation principles of DCM flyback converter are as follows:

Stage I

During the MOSFET on time (t_{ON}), input voltage (V_{DC}) is applied across the primary-side inductor (L_m). Then MOSFET current (I_{DS}) increases linearly from zero to the peak value (I_{PK}). During this time, the energy is drawn from the input and stored in the inductor.

Stage II

When the MOSFET (Q1) is turned off, the energy stored in the inductor forces the rectifier diode (D_F) to be turned on. While the diode is conducting, the output voltage (V_O), together with diode forward-voltage drop (V_F), is applied across the secondary-side inductor and the diode current (I_F) decreases linearly from the peak value ($I_{PK} \times N_P/N_S$) to zero. At the end of inductor current discharge time (I_{DIS}), all the energy stored in the inductor has been delivered to the output.

Stage III

When the diode current reaches zero, the transformer auxiliary winding voltage (V_A) begins to oscillate by the resonance between the primary-side inductor (L_m) and the effective capacitor loaded across MOSFET (Q1).

Constant Voltage Regulation

During the inductor current discharge time (t_{DIS}), the sum of output voltage (V_O) and diode forward-voltage drop (V_F) is reflected to the auxiliary winding side as (V_O+V_F) × N_A/N_S . Since the diode forward-voltage drop (V_F) decreases as current decreases, the auxiliary winding voltage (V_A) reflects the output voltage (V_O) at the end of diode conduction time (t_{DIS}), where the diode current (I_F) diminishes to zero. By sampling the winding voltage at the end of the diode conduction time (t_{DIS}), the output voltage (V_O) information can be obtained. The internal error amplifier for output voltage regulation (EAV) compares the sampled voltage with an internal precise reference to generate error voltage (V_{COMV}), which determines the duty cycle of the MOSFET (Q1) in Constant Voltage Mode.

Constant Current Regulation

The output current (I_O) can be estimated using the peak drain current (I_{PK}) and inductor current discharge time (t_{DIS}) since output current (I_O) is same as the average of the diode current (I_{F_AVG}) in steady state. The output current estimator $(I_O \ Estimator)$ determines the peak value of the drain current with a peak detection circuit and calculates the output current (I_O) using the inductor discharge time (t_{DIS}) and switching period (t_S) . This output information is compared with an internal precise reference to generate error voltage (V_{COMI}) , which determines the duty cycle of the MOSFET (Q1) in Constant Current Mode. With Fairchild's innovative technique TRUECURRENT®, constant current output can be precisely controlled.

Voltage and Current Error Amplifier

Of the two error voltages, V_{COMV} and V_{COMI} , the small one determines the duty cycle. Therefore, during Constant Voltage Regulation Mode, V_{COMV} determines the duty cycle while V_{COMI} is saturated to HIGH. During Constant Current Regulation Mode, V_{COMI} determines the duty cycle while V_{COMV} is saturated to HIGH.

Operating Current

The operating current is typically 3.2 mA. The small operating current results in higher efficiency and reduces the V_{DD} capacitor (C_{VDD}) requirement. Once FL663 enters Green Mode, the operating current is reduced to 0.95 mA, assisting the power supply in meeting power conservation requirements.

Green Mode Operation

The FL663 uses voltage regulation error amplifier output (V_{COMV}) as an indicator of the output load and modulates the PWM frequency, as shown in Figure 21. The switching frequency decreases with cycle skipping as load decreases. In heavy load conditions, the switching frequency is fixed at 50 kHz. Once V_{COMV} decreases below 2.5 V, the PWM frequency linearly decreases from 50 kHz. Once V_{COMV} decreases below V_{N} , the PWM frequency linearly decreases with cycle skipping from 50 kHz to reduce switching losses.

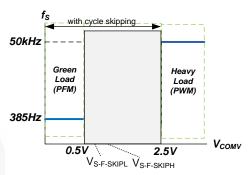


Figure 21. Switching Frequency as Output Load

Frequency Hopping

EMI reduction is accomplished by frequency hopping, which spreads the energy over a wider frequency range than the bandwidth measured by the EMI test equipment. FL663 has an internal frequency hopping circuit that changes the switching frequency between 47 kHz and 53 kHz.

High-Voltage Startup

0 shows the startup block. The HV pin is connected to the line input or DC link capacitor (C_{DC}). During startup, the internal startup circuit is enabled. Meanwhile, line input supplies the current (I_{Start}) to charge the V_{DD} capacitor (C_{VDD}). When the V_{DD} voltage reaches V_{DD-ON} (16 V) and V_{DC} is enough high to avoid brownout, the internal startup circuit is disabled, blocking I_{Start} from flowing into the HV pin. Once the IC turns on, C_{VDD} is the only energy source to supply the IC consumption current before the PWM starts to switch. Thus, C_{VDD} must be large enough to prevent V_{DD-OFF} (7.5 V) before the power can be delivered from the auxiliary winding. To avoid the surge from input source, the R_{Start} is connected between C_{DC} and HV, with a recommended value of 100 k Ω .

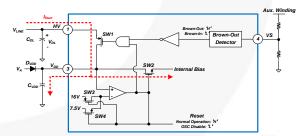


Figure 22. Startup Block

Protections

The FL663 has several self-protection functions; overvoltage protection, thermal shutdown protection, brownout protection, and pulse-by-pulse current limit.

V_{DD} Under-Voltage Lockout (UVLO)

The turn-on and turn-off thresholds are fixed internally at 16 V and 7.5 V, respectively. During startup, the V_{DD} capacitor (C_{VDD}) must be charged to 16 V. The V_{DD} capacitor (C_{VDD}) continues to supply V_{DD} until power can be delivered from the auxiliary winding of the main transformer. V_{DD} is not allowed to drop below 7.5 V during this startup process. This UVLO hysteresis window ensures that V_{DD} capacitor (C_{VDD}) properly supplies V_{DD} during startup.

V_{DD} Over-Voltage Protection (OVP)

The OVP prevents damage from over-voltage conditions. If the V_{DD} voltage exceeds 28 V at open-loop feedback condition, the OVP is triggered and the PWM switching is disabled. The OVP has a debounce time (typically 200 $\mu s)$ to prevent false triggering due to switching noises.

Thermal Shutdown Protection (TSD)

The built-in temperature-sensing circuit shuts down PWM output if the junction temperature exceeds 140°C. There is a hysteresis of 15°C.

Pulse-by-Pulse Current Limit

When the current sensing voltage (V_{CS}) across the current-sense resistor (R_{Sense}) of MOSFET (Q1) exceeds the internal threshold of 0.8 V, the MOSFET (Q1) is turned off for the remainder of switching cycle. In normal operation, the pulse-by-pulse current limit is not triggered because the peak current is limited by the control loop.

Leading-Edge Blanking (LEB)

Each time the power MOSFET (Q1) switches on, a turnon spike occurs at the sense resistor (R_{Sense}). To avoid premature termination of the switching pulse, a leadingedge blanking time is built in. Conventional RC filtering can be omitted. During this blanking period, the currentlimit comparator is disabled and cannot switch off the gate driver.

Gate Output

The FL663 output stage is a fast totem-pole gate driver. Cross conduction has been avoided to minimize heat dissipation, increase efficiency, and enhance reliability. The output driver is clamped by an internal 15 V Zener diode to protect power MOSFET transistors against undesired over-voltage gate signals.

Built-in Slope Compensation

The sensed voltage across the current-sense resistor is used for Current Mode control and pulse-by-pulse current limiting. Built-in slope compensation improves stability and prevents sub-harmonic oscillations due to peak-current mode control. The FL663 has a synchronized, positive-slope ramp built-in at each switching cycle.

Noise Immunity

Noise from the current sense or the control signal can cause significant pulse-width jitter, particularly in Continuous-Conduction Mode. While slope compensation helps alleviate these problems, further precautions should still be taken. Good placement and layout practices should be followed. Avoiding long PCB traces and component leads, locating compensation and filter components near the FL663, and increasing the power MOSFET gate resistance are advised.

Operation Area

Figure 23 shows operation area. FL663 has two switching frequency (f_S) in Constant Current Mode. One is 50 kHz. In this case, FL663 can be operated with best condition for LED illumination. The output voltage range is between normal output voltage (V_O^N) and 50% of normal output voltage (V_O^N). The other is 33 kHz. When the output voltage is dropped by decreasing the number of LEDs, the output voltage (V_O^N) drops under 50% of normal voltage (V_O^N). At that time, V_{DD} drops to near UVLO protection and triggers protection. To avoid 33 kHz, V_O^N should be designed with enough margin.

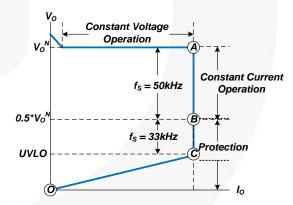


Figure 23. Operation Area



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